



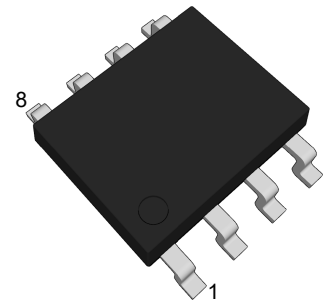
PJM08C30PA

N and P-Channel Complementary Power MOSFET

Product Summary

- **N-Channel**
- $V_{DS} = 30V, I_D = 8A$
- $R_{DS(on)} < 31m\Omega @ V_{GS} = 10V$
- $R_{DS(on)} < 40m\Omega @ V_{GS} = 4.5V$
- **P-Channel**
- $V_{DS} = -30V, I_D = -7A$
- $R_{DS(on)} < 60m\Omega @ V_{GS} = -10V$
- $R_{DS(on)} < 87m\Omega @ V_{GS} = -4.5V$

SOP-8



(Top View)

Features

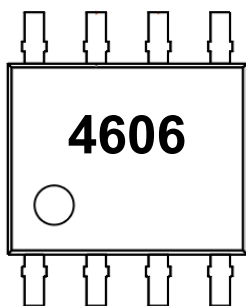
- Advanced Trench Technology
- RoHS and Reach Compliant
- Halogen and Antimony Free
- Moisture Sensitivity Level 3

Pin	Description	Pin	Description
1	Source1	4	Gate2
2	Gate1	5,6	Drain2
3	Source2	7,8	Drain1

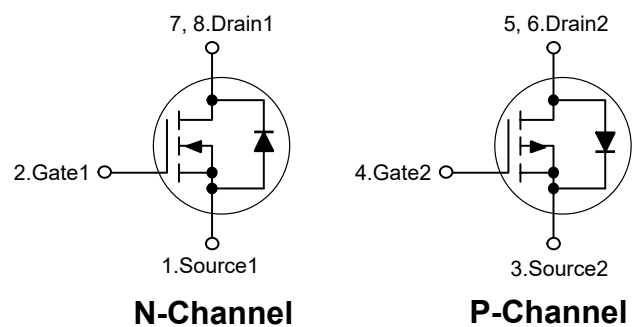
Application

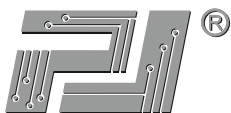
- Power Management

Marking Code



Schematic Diagram





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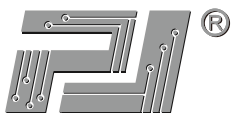
Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	±20		V
Drain Current-Continuous	I_D	8	-7	A
Drain Current-Pulsed ^{Note1}	I_{DM}	20	-20	A
Maximum Power Dissipation	P_D	2		W
Junction Temperature	T_J	150		°C
Storage Temperature Range	T_{STG}	-55 to +150		°C

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	62.5	°C/W
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N-Channel

Electrical Characteristics

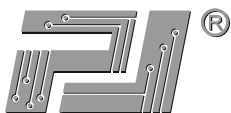
($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	--	--	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	--	--	± 100	nA
Gate Threshold Voltage ^{Note3}	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.6	2.4	V
Drain-Source On-Resistance ^{Note3}	$R_{DS(on)}$	$V_{GS}=10V, I_D=5A$	--	25	31	m Ω
		$V_{GS}=4.5V, I_D=5A$	--	32	40	m Ω
Forward Transconductance ^{Note3}	g_{FS}	$V_{DS}=5V, I_D=5A$	--	15	--	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	--	485.8	--	pF
Output Capacitance	C_{oss}		--	65.2	--	pF
Reverse Transfer Capacitance	C_{rss}		--	54	--	pF
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=5.8A, V_{GS}=10V$	--	12.6	--	nC
Gate-Source Charge	Q_{gs}		--	1.9	--	nC
Gate-Drain Charge	Q_{gd}		--	2.6	--	nC
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, R_L=3\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	--	5	--	nS
Turn-on Rise Time	t_r		--	3	--	nS
Turn-off Delay Time	$t_{d(off)}$		--	15	--	nS
Turn-off Fall Time	t_f		--	3.5	--	nS
Source-Drain Diode Characteristics						
Diode Forward Voltage ^{Note3}	V_{SD}	$V_{GS}=0V, I_S=8A$	--	--	1.2	V
Diode Forward Current ^{Note2}	I_S		--	--	8	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

**P-Channel****Electrical Characteristics**(T_a=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	-V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	30	--	--	V
Zero Gate Voltage Drain Current	-I _{DSS}	V _{DS} =-30V, V _{GS} =0V	--	--	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
Gate Threshold Voltage ^{Note3}	-V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	1	1.4	3	V
Drain-Source On-Resistance ^{Note3}	R _{DS(on)}	V _{GS} =-10V, I _D =-4.1A	--	48	60	mΩ
		V _{GS} =-4.5V, I _D =-3A	--	60	87	mΩ
Forward Transconductance ^{Note3}	g _{FS}	V _{DS} =-5V, I _D =-4A	5.5	--	--	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, f=1MHz	--	650	--	pF
Output Capacitance	C _{oss}		--	105	--	pF
Reverse Transfer Capacitance	C _{rss}		--	65	--	pF
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-4.1A, V _{GS} =-10V	--	12.5	--	nC
Gate-Source Charge	Q _{gs}		--	2.8	--	nC
Gate-Drain Charge	Q _{gd}		--	2.7	--	nC
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, R _L =3.6Ω V _{GS} =-10V, R _{GEN} =3Ω	--	8.5	--	nS
Turn-on Rise Time	t _r		--	4.5	--	nS
Turn-off Delay Time	t _{d(off)}		--	26	--	nS
Turn-off Fall Time	t _f		--	12.5	--	nS
Source-Drain Diode Characteristics						
Diode Forward Voltage ^{Note3}	-V _{SD}	V _{GS} =0V, I _S =-7A	--	--	1.2	V
Diode Forward Current ^{Note2}	-I _S		--	--	7	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t ≤ 10 sec.

3. Pulse Test: Pulse width ≤ 300μs, duty cycle ≤ 2%

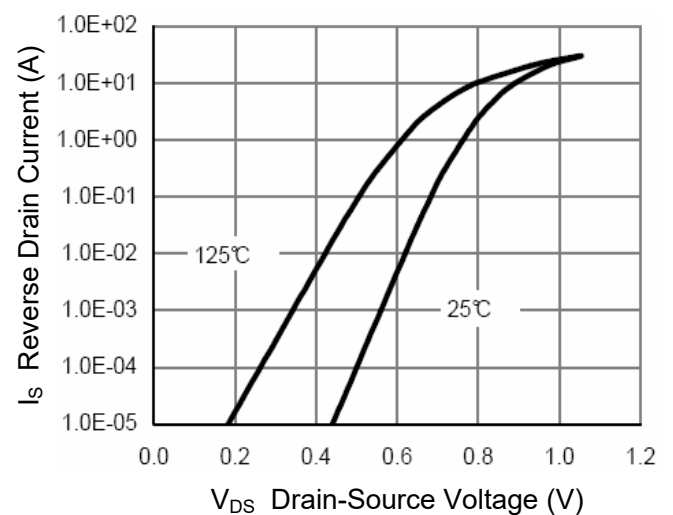
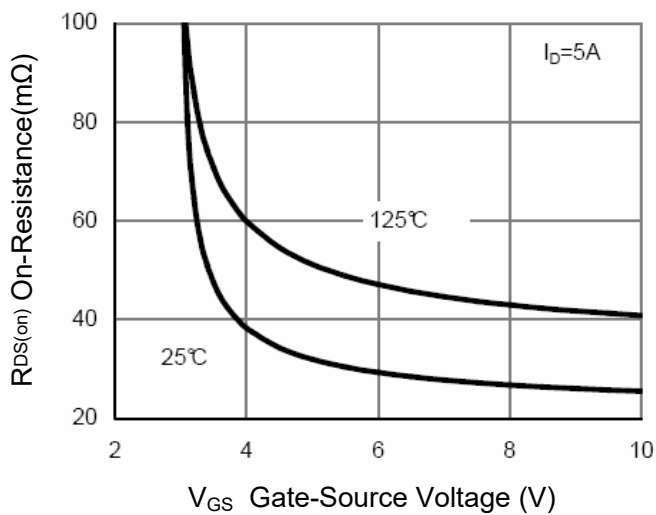
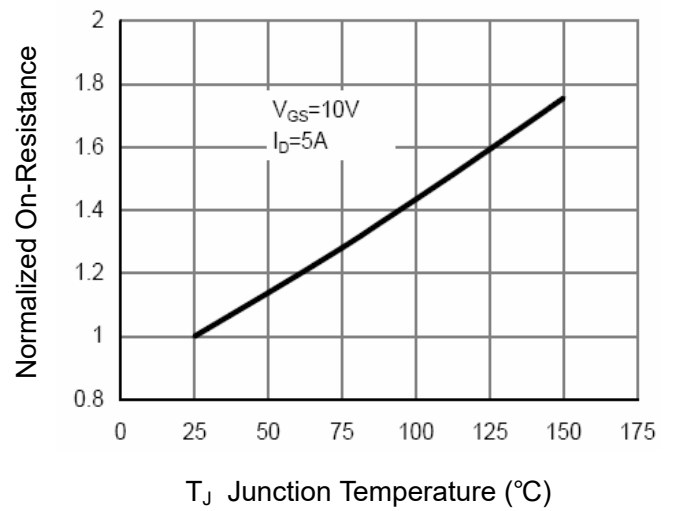
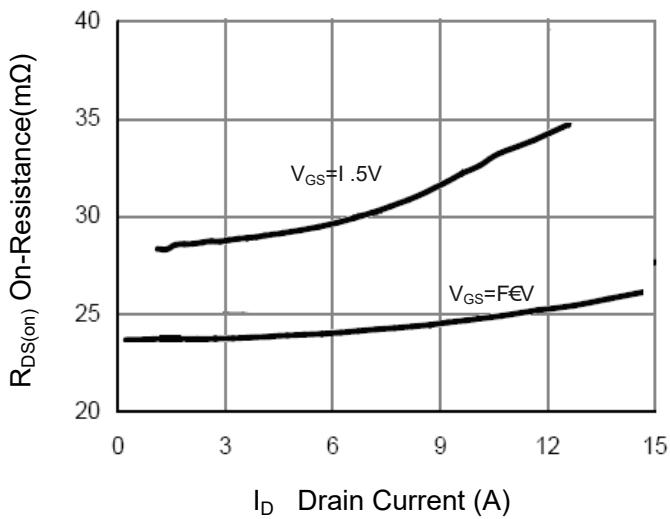
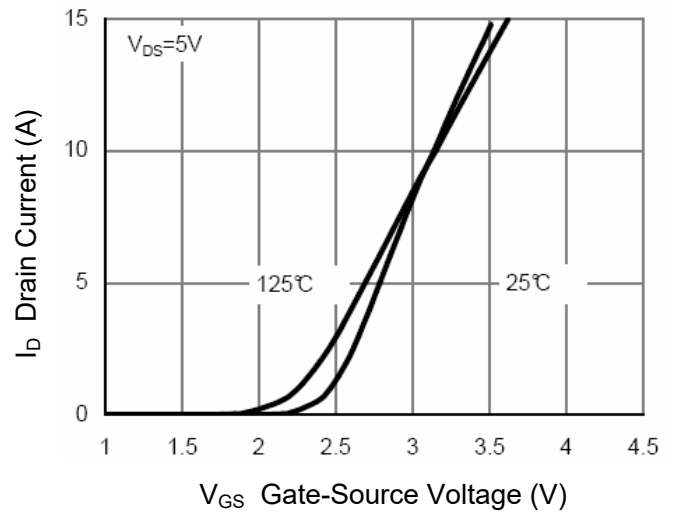
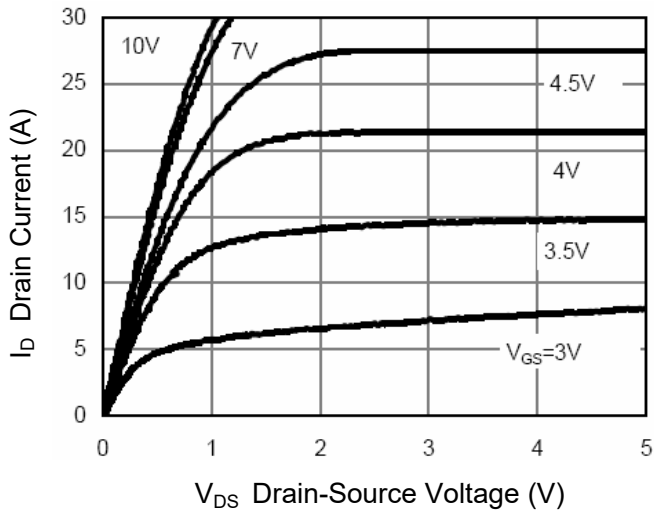


PJM08C30PA

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N-Channel

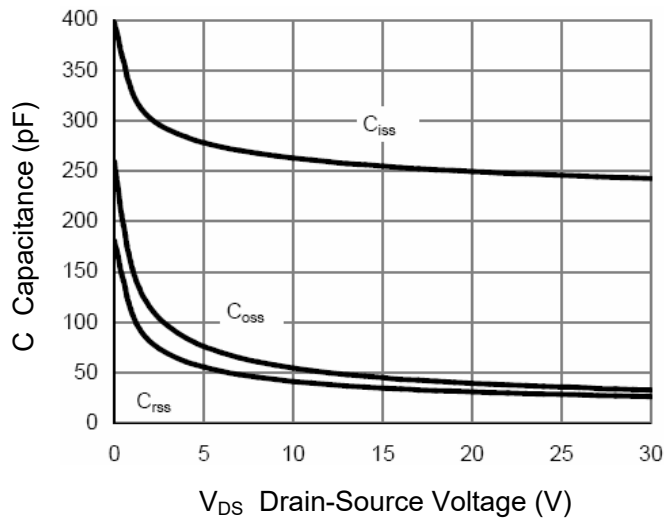
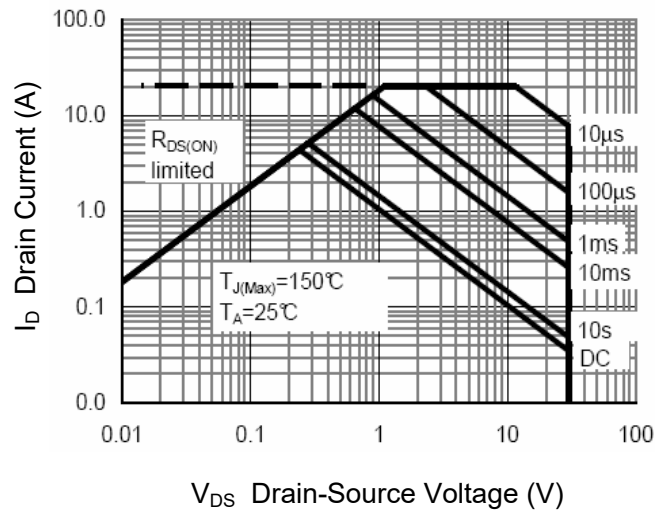
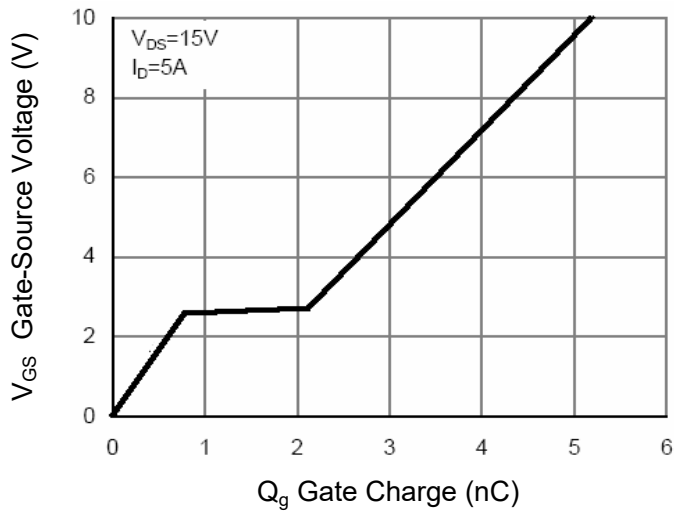
Typical Characteristics Curves





PJM08C30PA

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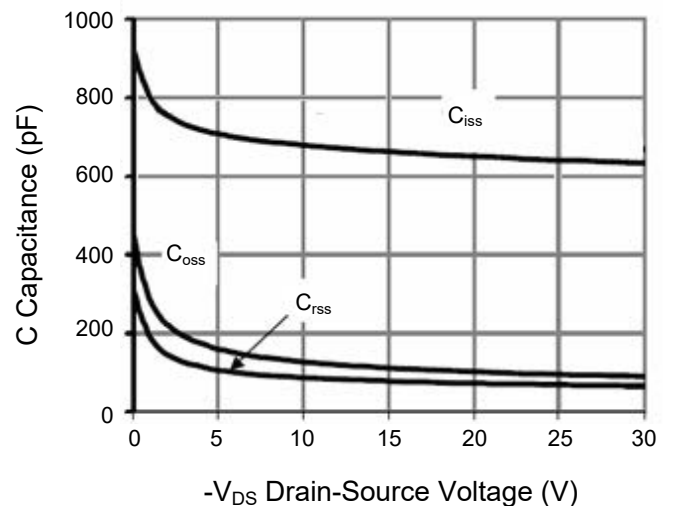
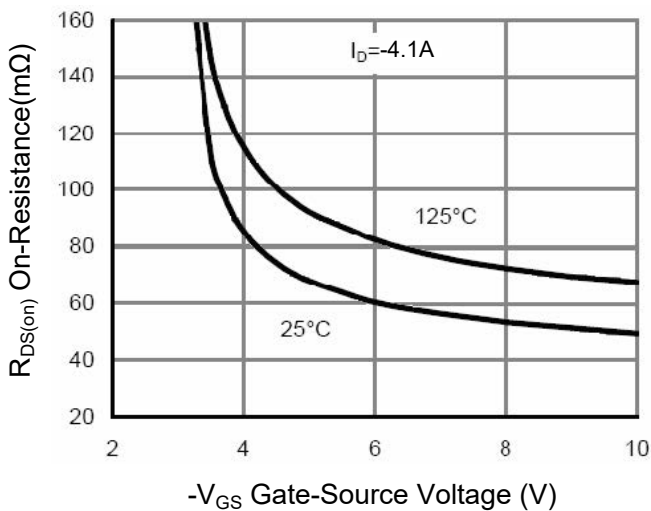
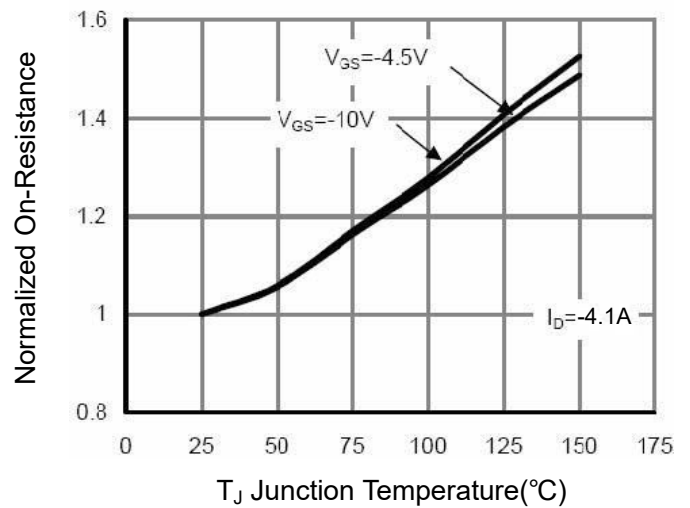
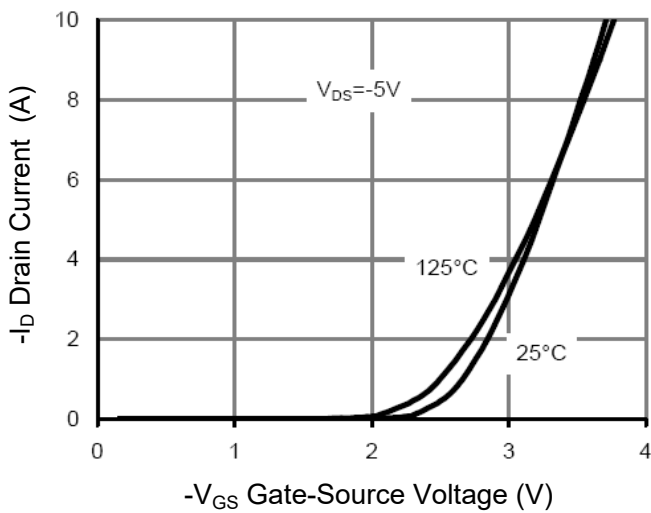
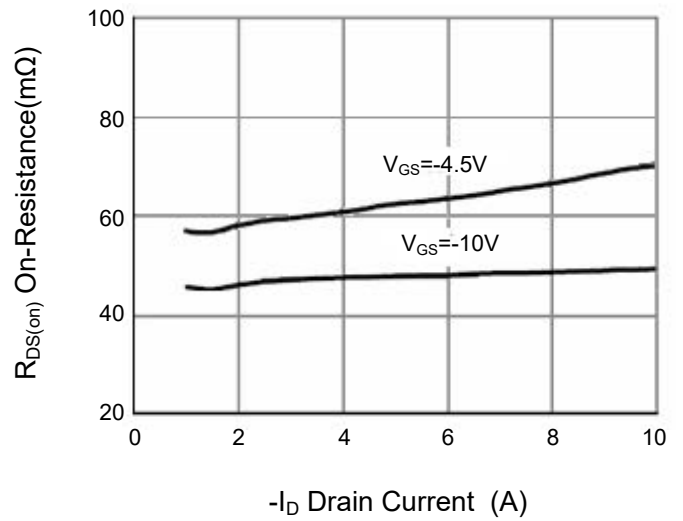
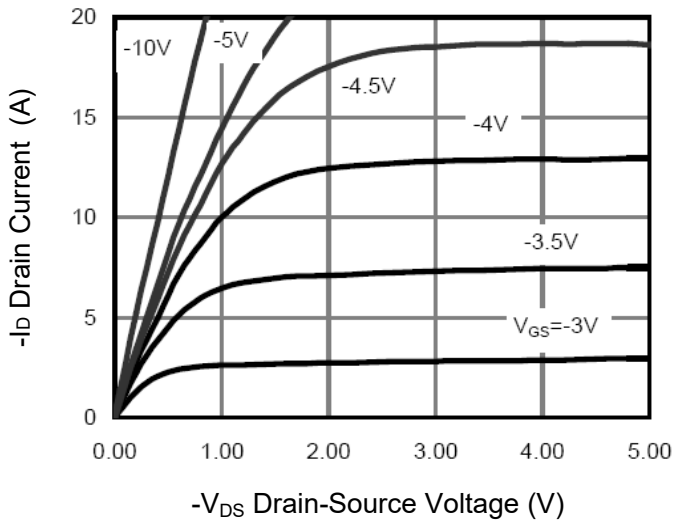


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P-Channel

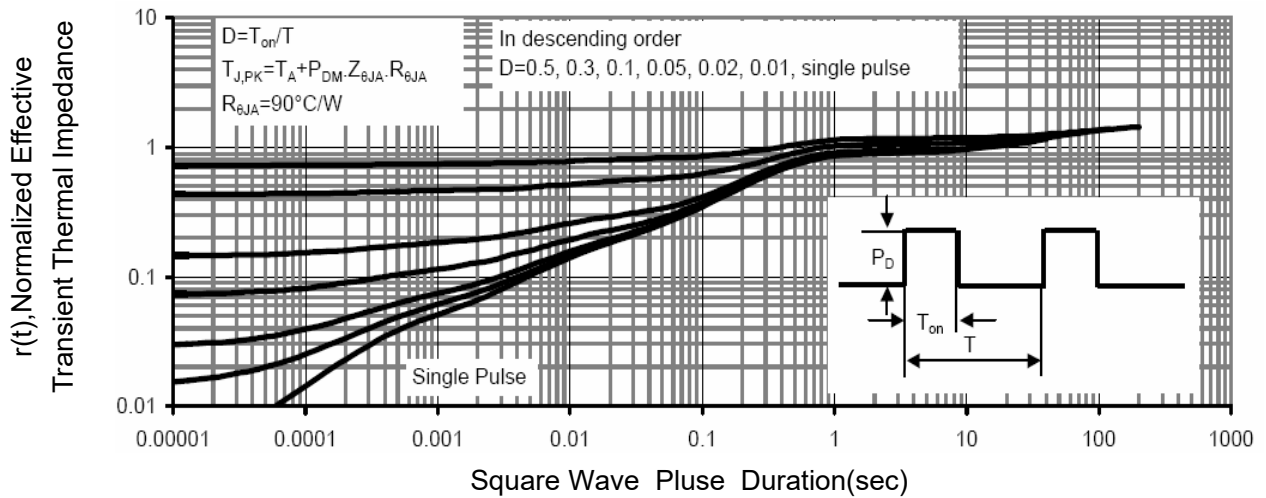
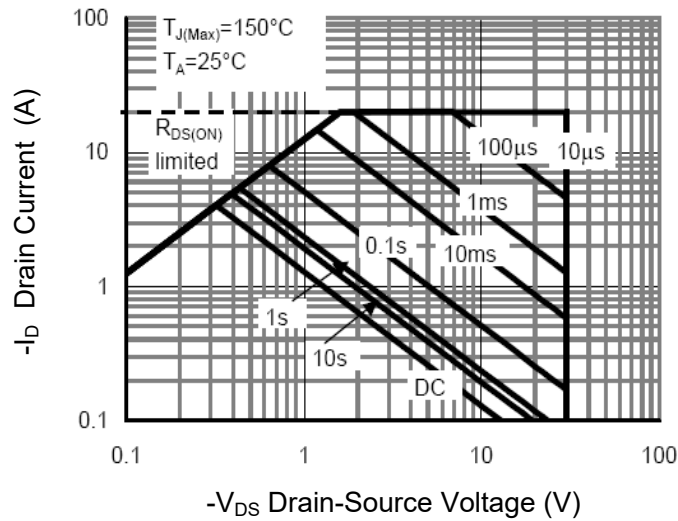
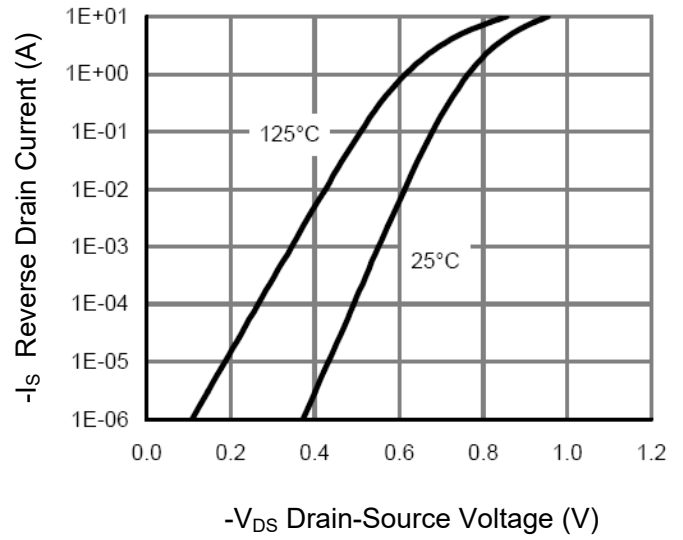
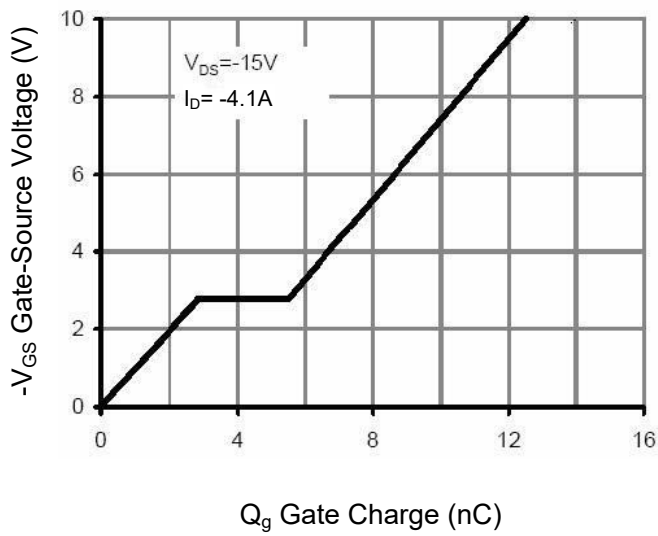
Typical Characteristics Curves





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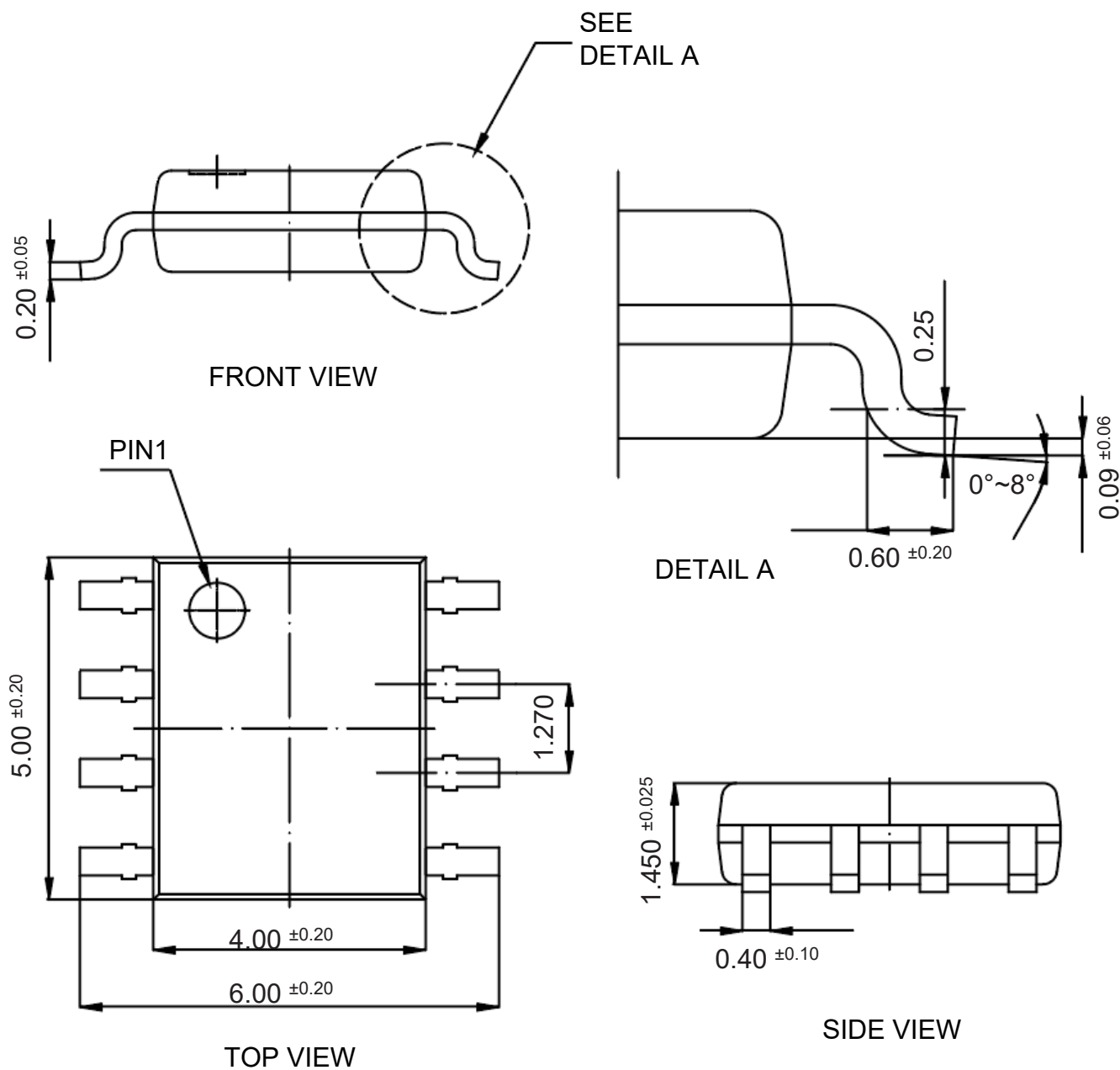
PJM08C30PA

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Package Outline

SOP-8

Dimensions in mm



Ordering Information

Device	Package	Shipping
PJM08C30PA	SOP-8	4,000PCS/Reel&13inches